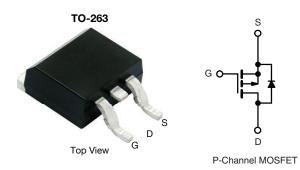
SQM40031EL

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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY						
V _{DS} (V)	-40					
$R_{DS(on)}$ (Ω) at V_{GS} = -10 V	0.00300					
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = -4.5 V	0.00380					
I _D (A)	-120					
Configuration	Single					
Package	TO-263					

FEATURES

- TrenchFET[®] power MOSFET
- · Package with low thermal resistance
- 100 % Rg and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	-40	N/		
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current ^a	T _C = 25 °C	1	-120	A		
Continuous Drain Current ~	T _C = 125 °C	ID	-120			
Continuous Source Current (Diode conduction) ^a		I _S	-120			
Pulsed Drain Current ^b	I _{DM}	-300				
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-60			
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	180	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	D	375	W		
	T _C = 125 °C	PD	125	vv		
Operating Junction and Storage Temperature Rar	nge	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB mount ^c	R _{thJA}	40	- °C/W		
Junction-to-Case (Drain)		R _{thJC}	0.4			

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR4 material).

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \ \mu A$		-40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$		-1.5	-2.0	-2.5	v	
Gate-Source Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA	
		$V_{GS} = 0 V$	$V_{DS} = -40 V$	-	-	-1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -40 V, T_J = 125 °C	-	-	-50		
		$V_{GS} = 0 V$	V_{DS} = -40 V, T _J = 175 °C	-	-	-450	1	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -10 V$	$V_{DS} \le -5 V$	-100	-	-	Α	
		$V_{GS} = -10 \text{ V}$	I _D = -30 A	-	0.00250	0.00300	Ω	
Drain-Source On-State Resistance ^a	В	$V_{GS} = -10 V$	I _D = -30 A, T _J = 125 °C	-	-	0.00440		
Drain-Source On-State Resistance ~	R _{DS(on)}	V _{GS} = -10 V	I _D = -30 A, T _J = 175 °C	-	-	0.00520		
		$V_{GS} = -4.5 V$	I _D = -25 A	-	0.00316	0.00380	1	
Forward Transconductance b	9 _{fs}	V _{DS} = -15 V, I _D = -25 A		-	123	-	S	
Dynamic ^b	•	·						
Input Capacitance	C _{iss}		V _{DS} = -25 V, f = 1 MHz	-	30 000	39 000	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	1850	2500		
Reverse Transfer Capacitance	C _{rss}	1		-	1550	2100		
Total Gate Charge ^c	Qg			-	527	800		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = -10 V$	$V_{DS} = -20 \text{ V}, \text{ I}_{D} = -80 \text{ A}$	-	89	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1		-	100	-		
Gate Resistance	Rg	f = 1 MHz		1	2.26	3.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	21	35		
Rise Time ^c	t _r	V _{DD} =	-20 V, R _L = 0.3 Ω	-	30	50		
Turn-Off Delay Time ^c	t _{d(off)}	I _D ≅ -80 A,	$I_D \cong -80$ Å, $V_{GEN} = -10$ V, $R_g = 1 \Omega$		250	400	ns	
Fall Time ^c	t _f	1			165	300		
Source-Drain Diode Ratings and Cha	racteristics ^b					•		
Pulsed Current ^a	I _{SM}			-	-	-300	Α	
Forward Voltage	V _{SD}	I _F = -80 A, V _{GS} = 0 V		-	-0.85	-1.5	V	
Body diode reverse recovery time	t _{rr}	I _F = -50 A, di/dt = 100 A/μs		-	70	140	ns	
Body diode reverse recovery charge	Q _{rr}			-	134	270	nC	
Reverse recovery fall time	t _a			-	43	-	ns	
Reverse recovery rise time	t _b			-	35	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-4	-8	A	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

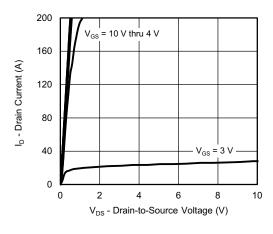
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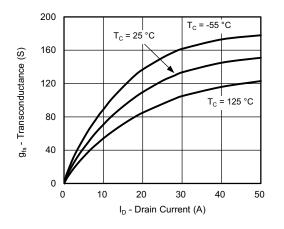
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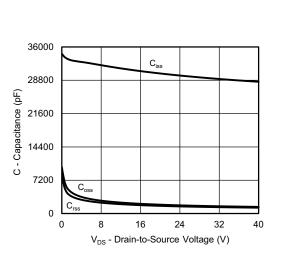
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



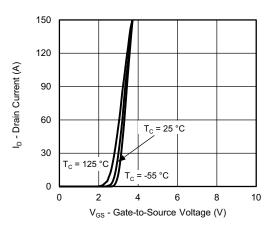
Output Characteristics



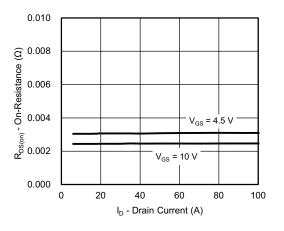
Transconductance



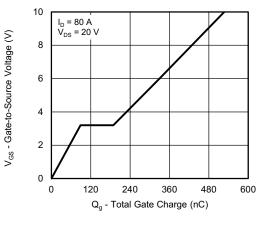
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S17-0071-Rev. A, 23-Jan-17

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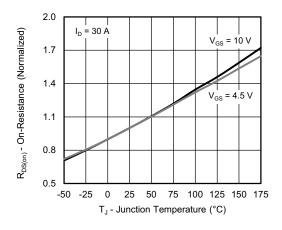
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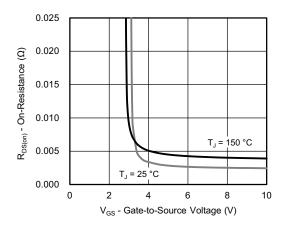


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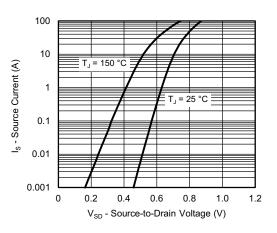
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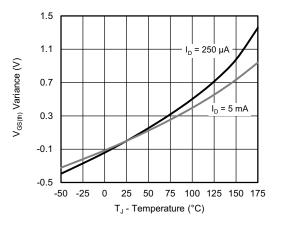
On-Resistance vs. Junction Temperature



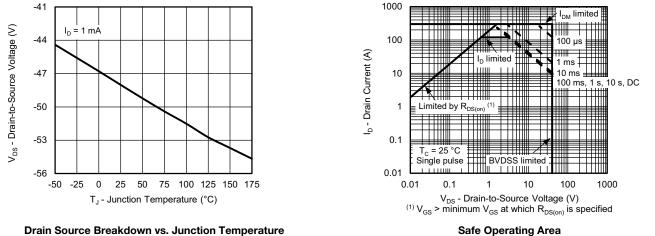
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

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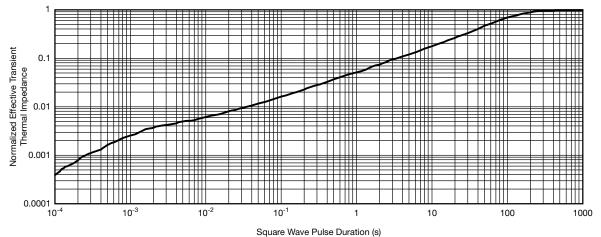
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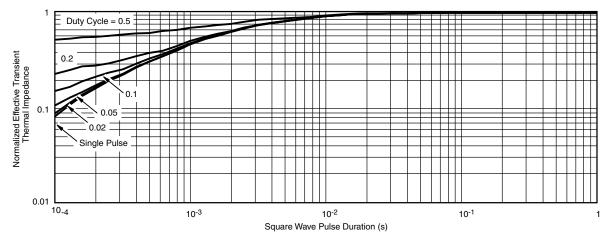


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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN. MAX.		MIN.	MAX.	
A		0.160	0.190	4.064	4.826	
b		0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
E1		0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
е		0.100	BSC	2.54 BSC		
	К	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010	0.010 BSC		BSC	
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
 - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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